新芯微电子
NewChip
Microelectronics

DR5000 THRU DR5010

特性：FEATURES

◆正向压降低.Low forward voltage drop

◆低漏电. Low leakage current

◆高浪涌承受能力.High surge current capability

◆35A 工作在表面温度是125℃,无热损耗的情况下.

35Ampere Operation At TL=125℃ With No Thermal Runaway

机械性能：MECHANICAL DATA

◆封装:铜材质. Case: Copper

◆端子:镀金端子,焊接按照 MIL-STD-202,方法 208.

Terminals: Plated terminals, solderable per

MIL-STD-202, method 208.

◆极性: 灌注红色环氧树脂（端子为正/P 型）

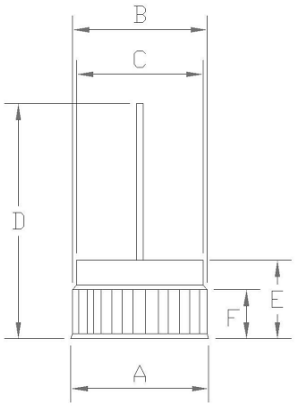
灌注黑色环氧树脂（端子为负/N 型）

Polarity : By RED Color Epoxy Potting. (Positive)

By BLACK Color Epoxy Potting. (Negative)

◆重量：6.8 克. Weight: 6.8grams

BOSCH



A=⌀13.0±0.2mm　　B=⌀12.76±0.02mm
C=⌀11.4±0.2mm　　D=25.0mm
E=7.90±0.2mm　　F=4.15%%0.20mm

Dimension in millimeters

极限值和电参数

TA= 25℃除非另有规定. 单相,正半弦波,60HZ,阻抗或电感负载.为电容装载,减少电流的 20%

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25℃ Ambient temp. Unless otherwise specified.Single phase, half sine wave, 60HZ,resistive or inductive load.

型 号 TYPE	符 号	DR5000	DR5001	DR5002	DR5004	DR5006	DR5008	DR5010	单 位
最大峰值反向电压 Maximum Current Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
最大反向有效值电压 Working Peak Reverse Voltage	V_{RMS}	35	70	140	280	420	560	700	V
最大直流截止电压 Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
最大正向平均整流电流Ta=125℃, Maximum Average Forward Rectified Current	$I_{F(AV)}$	50							A
峰值正向浪涌电流 Peak Forward Surge Current 8.3ms Single Sine-wave on Rated Load (JEDEC Method)	I_{FSM}	500							A
最大瞬间正向压降@100A Maximum Instantaneous Forward Voltage Drop at 100A DC	V_F	1.03							V
最大反向直流电流 Maximum DC Reverse Current Ta = 25℃ at Rated DCBlocking Voltage Ta =100℃	I_R	1.0 200							μA
典型结电容 Typical Junction Capacitance (NOTE 1)	C_J	140							pF
工作及储存温度范围 Operating AND Storage Temperature Range	T_J,T_{STG}	-55～+150							℃

注 释 : NOTE 在 1MHz 下测量，施加 4.0V D.C 的反向电压. Measured at 1 MHz and Applied Reverse Voltage of 4.0 Volts D.C.

FIG. 1 –最大正向平均电流降额

FIG. 1 –MAXIMUM AVERAGE FORWARD CURRENT DERATING

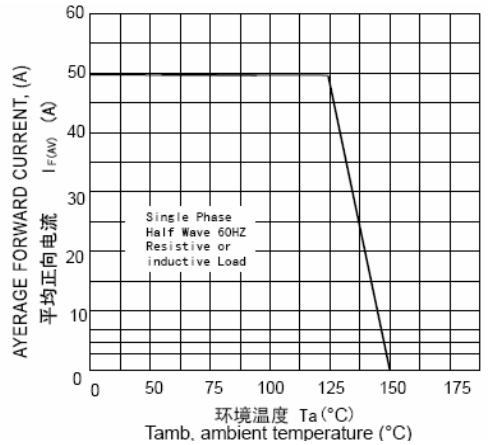


FIG. 2 –最大非重复正向浪涌电流

FIG. 2 –MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

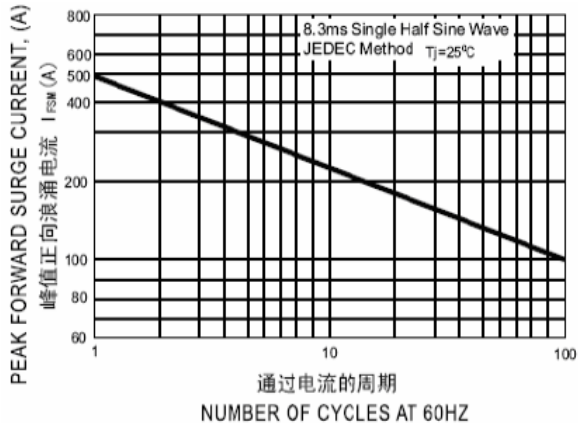


FIG. 3 –反向特性曲线(典型)

FIG. 3 – TYPICA REVERSE CHARACTERISTICS.

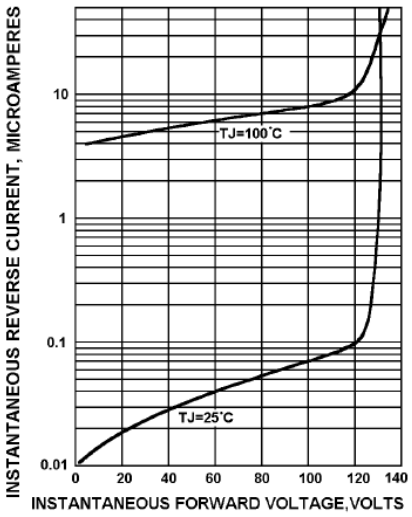


FIG. 4–正向特性曲线(典型)

FIG.4 – TYPICA FORWARD CHARACTERISTICS

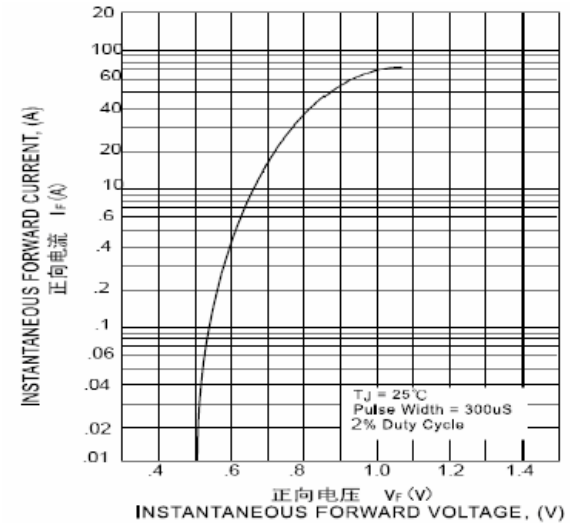


FIG.5–结电容特性曲线

FIG.5–TYPICAL JUNCTION CAPACITANCE